

30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-30 A

Features

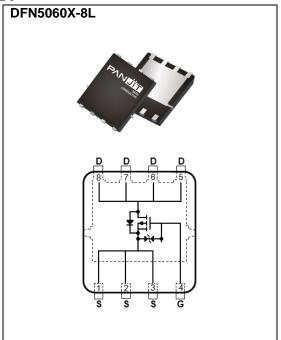
- RDS(ON), VGS@-10V, ID@-20A<18.8m Ω
- RDS(ON), VGS@-4.5V, ID@-10A<30.7m Ω
- 100% UIS tested
- Reliable and Rugged
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060X-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.087 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current ^(Note 3)	T _C =25°C	l _D	-30	
	Tc=100°C		-19	Α
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-98	
Power Dissipation	T _C =25°C	-	28	10/
	T _C =100°C	Po	11	W
Continuous Drain Current(Note 4)	T _A =25°C	I _D	-9.6	
	T _A =70°C		-7.7	A
Power Dissipation	T _A =25°C	5	2.8	10/
	T _A =70°C	Po	1.8	W
Single Pulse Avalanche Energy(Note 5)		Eas	42	mJ
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Thermal Resistance ^(Note 4)	Junction to Case	R _{0JC}	4.5	°C/W
	Junction to Ambient	$R_{\theta JA}$	45	C/VV



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.8	-2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A	-	15	18.8	mΩ	
		V _{GS} =-4.5V, I _D =-10A	-	23.6	30.7		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA	
Cata Sauraa Laaka aa Currant		V _{GS} =±25V, V _{DS} =0V	-	-	±10	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1		
Dynamic ^(Note 6)		<u></u>	1				
Total Gate Charge	Q_g	V _{DS} =-24V, I _D =-20A, V _{GS} =-10V	-	22	-	nC	
Gate-Source Charge	Q_{gs}		-	3	-		
Gate-Drain Charge	Q_{gd}		-	7	-		
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V,	-	1009	-	pF	
Output Capacitance	Coss		-	143	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	119	-		
Gate resistance	Rg	f=1MHz	-	10.4	-	Ω	
Turn-On Delay Time	td _(on)	V_{DS} =-24V, I_{D} =-20A, V_{GS} =-10V, R_{G} =3 Ω	-	7	-	ns	
Turn-On Rise Time	tr		-	3	-		
Turn-Off Delay Time	td _(off)		-	36	-		
Turn-Off Fall Time	tf	(11016-2)	-	40	-		
Drain-Source Diode							
Diode Forward Current	Is	Tc=25°C	-	-	-30	A	
Pulsed Diode Forward Current	I _{SM}	10=25 U	-	-	-98		
Diode Forward Voltage	V _{SD}	Is=-20A, V _{GS} =0V	-	-0.9	-1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =-20A	-	16	-	ns	
Reverse Recovery Charge	Qrr	dl _S /dt=100A/us	-	8	-	nC	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=-13A, V_{DD}=-30V, V_{GS}=-10V, Starting T_J=25°C.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

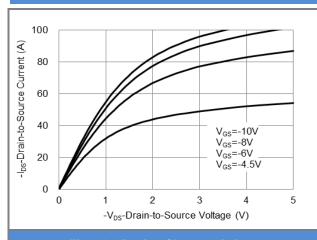
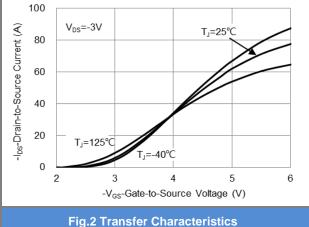


Fig.1 On-Region Characteristics



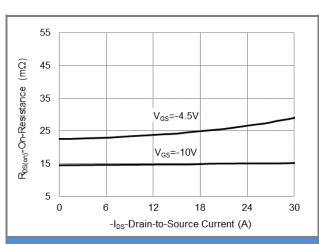


Fig.3 On-Resistance vs. Drain Current

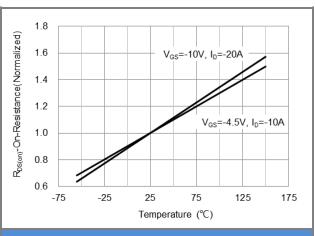
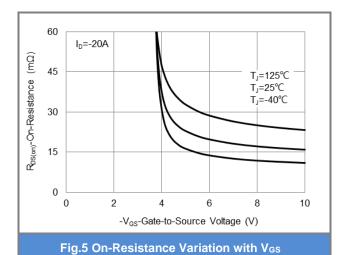
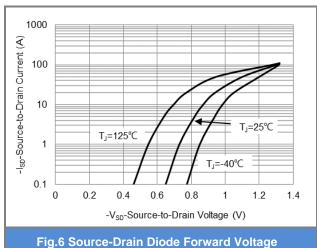


Fig.4 On-Resistance vs. Junction temperature







TYPICAL CHARACTERISTIC CURVES

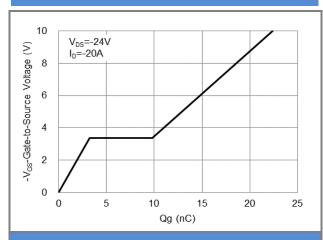


Fig.7 Gate-Charge Characteristics

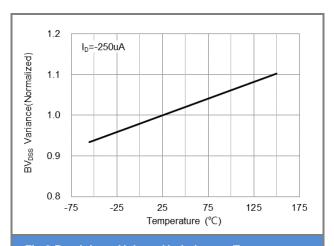


Fig.8 Breakdown Voltage Variation vs. Temperature

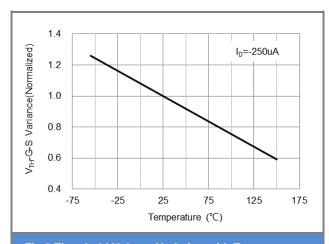


Fig.9 Threshold Voltage Variation with Temperature

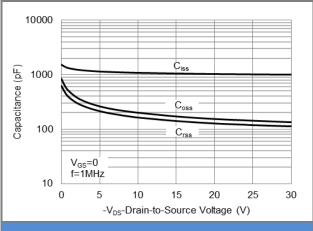
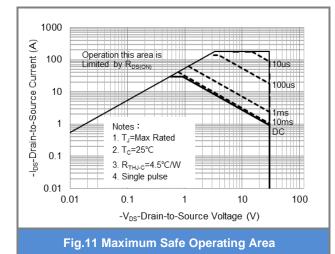


Fig.10 Capacitance vs. Drain-Source Voltage



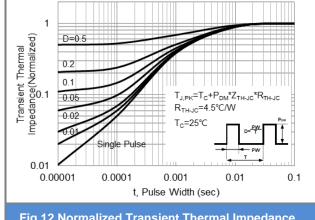


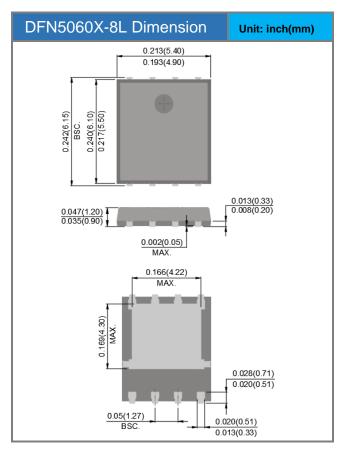
Fig.12 Normalized Transient Thermal Impedance

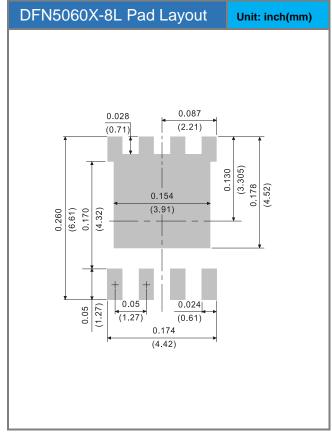


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5439E	DFN5060X-8L	3K pcs / 13" reel	Q5439E	

Packaging Information & Mounting Pad Layout







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